2N5401

Amplifier Transistors

PNP Silicon

Features

• These are Pb-Free Devices*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector - Emitter Voltage	V _{CEO}	150	Vdc
Collector - Base Voltage	V _{CBO}	160	Vdc
Emitter - Base Voltage	V _{EBO}	5.0	Vdc
Collector Current - Continuous	I _C	600	mAdc
Total Device Dissipation @ T _A = 25°C Derate above 25°C	P _D	625 5.0	mW mW/°C
Total Device Dissipation @ T _C = 25°C Derate above 25°C	P _D	1.5 12	W mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150	°C

THERMAL CHARACTERISTICS

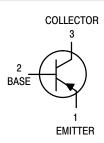
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	83.3	°C/W

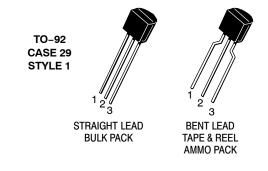
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



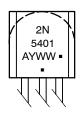
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MARKING DIAGRAM



A = Assembly Location

Y = Year WW = Work Week

= Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS	•		•	
Collector – Emitter Breakdown Voltage (Note 1) $(I_C = 1.0 \text{ mAdc}, I_B = 0)$	V _{(BR)CEO}	150	_	Vdc
Collector–Base Breakdown Voltage ($I_C = 100 \mu Adc, I_E = 0$)	V _{(BR)CBO}	160	_	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10 \mu Adc, I_C = 0$)	V _{(BR)EBO}	5.0	-	Vdc
Collector Cutoff Current $(V_{CB} = 120 \text{ Vdc}, I_E = 0)$ $(V_{CB} = 120 \text{ Vdc}, I_E = 0, T_A = 100^{\circ}\text{C})$	I _{CBO}	- -	50 50	nAdc μAdc
Emitter Cutoff Current $(V_{EB} = 3.0 \text{ Vdc}, I_C = 0)$	I _{EBO}	-	50	nAdc
ON CHARACTERISTICS (Note 1)	<u>.</u>			
DC Current Gain	h _{FE}	50 60 50	- 240 -	-
Collector–Emitter Saturation Voltage $ \begin{pmatrix} I_C = 10 \text{ mAdc}, I_B = 1.0 \text{ mAdc} \\ I_C = 50 \text{ mAdc}, I_B = 5.0 \text{ mAdc} \end{pmatrix} $	V _{CE(sat)}	- -	0.2 0.5	Vdc
Base – Emitter Saturation Voltage ($I_C = 10 \text{ mAdc}$, $I_B = 1.0 \text{ mAdc}$) ($I_C = 50 \text{ mAdc}$, $I_B = 5.0 \text{ mAdc}$)	V _{BE(sat)}	- -	1.0 1.0	Vdc
SMALL-SIGNAL CHARACTERISTICS	•		•	
Current-Gain — Bandwidth Product (I _C = 10 mAdc, V _{CE} = 10 Vdc, f = 100 MHz)	f _T	100	300	MHz
Output Capacitance (V _{CB} = 10 Vdc, I _E = 0, f = 1.0 MHz)	C _{obo}	-	6.0	pF
Small–Signal Current Gain ($I_C = 1.0 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}, f = 1.0 \text{ kHz}$)	h _{fe}	40	200	-
Noise Figure (I _C = 250 μ Adc, V _{CE} = 5.0 Vdc, R _S = 1.0 k Ω , f = 1.0 kHz)	NF	-	8.0	dB

^{1.} Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

ORDERING INFORMATION

Device	Package	Shipping [†]
2N5401G	TO-92 (Pb-Free)	5000 Unit / Bulk
2N5401RLRAG	TO-92 (Pb-Free)	2000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

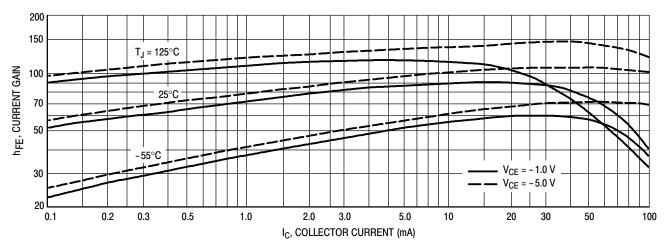


Figure 1. DC Current Gain

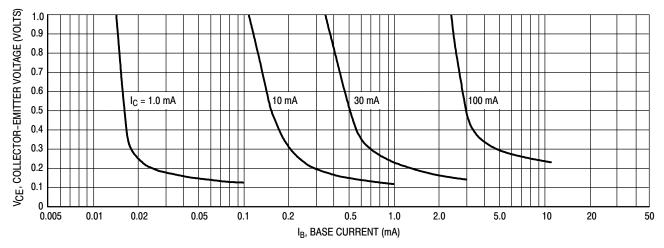


Figure 2. Collector Saturation Region

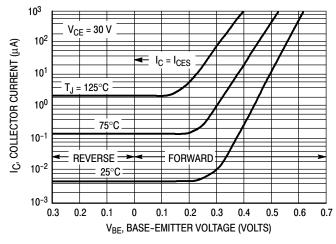


Figure 3. Collector Cut-Off Region

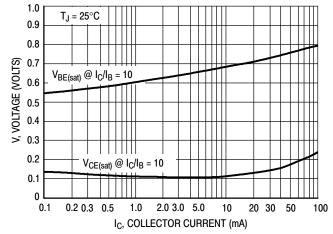


Figure 4. "On" Voltages

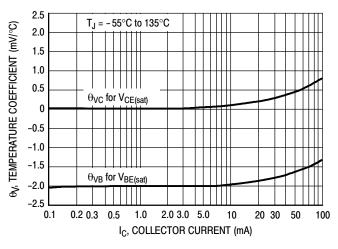


Figure 5. Temperature Coefficients

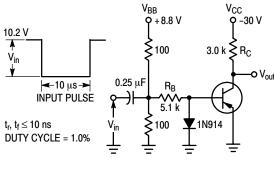


Figure 6. Switching Time Test Circuit

Values Shown are for $\rm I_{\rm C}$ @ 10 mA

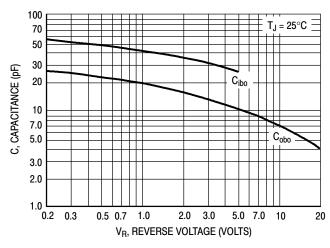


Figure 7. Capacitances

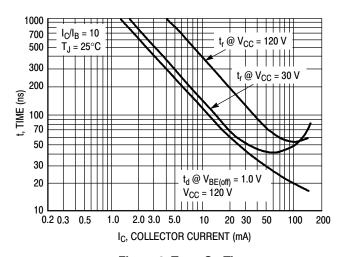


Figure 8. Turn-On Time

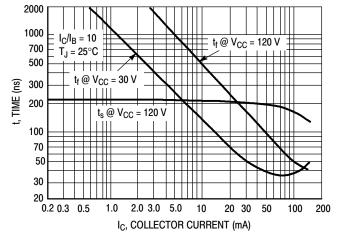


Figure 9. Turn-Off Time

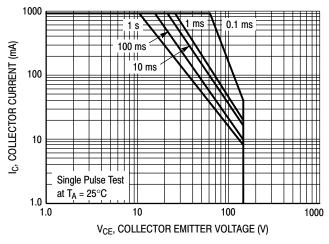
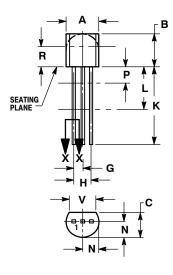


Figure 10. Safe Operating Area

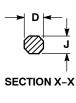
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PACKAGE DIMENSIONS

TO-92 (TO-226) CASE 29-11 **ISSUE AM**



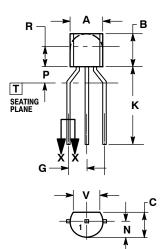
STRAIGHT LEAD **BULK PACK**



NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: INCH.
- CONTOUR OF PACKAGE BEYOND DIMENSION R
 IS UNCONTROLLED.
- LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
С	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
Р		0.100		2.54
R	0.115		2.93	
V	0 135		3 43	



BENT LEAD TAPE & REEL AMMO PACK



NOTES:

- 11. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994. 2. CONTROLLING DIMENSION:
- MILLIMETERS.
- MILLIMETERS.
 CONTOUR OF PACKAGE BEYOND
 DIMENSION R IS UNCONTROLLED.
 LEAD DIMENSION IS UNCONTROLLED IN
 P AND BEYOND DIMENSION K MINIMUM.
 - **MILLIMETERS** DIM MIN MAX 5.20 5.33 Α 4.45 В 4.32 4.19 3.18 D 0.40 0.54 2.40 0.39 G 2.80 12.70 N P 2.04 1.50 2.66 4.00

2.93

PIN 1. EMITTER

BASE

COLLECTOR

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